SCH1337

Power MOSFET -30V, 150mΩ, -2A, Single P-Channel

This Low-profile High-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

Features

- Low On-Resistance
- 4V drive
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mmt)

Typical Applications

- LCD Driver
- Load Switch
- Voltage Protection

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	-2	А
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	-8	А
Power Dissipation When mounted on ceramic substrate ($900mm^2 \times 0.8mm$)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

be assumed, damage may occur and reliability may be affected. 2 : This product is designed to "ESD immunity<200V*", so please take care when handling. *Machine Model

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit	
Junction to Ambient When mounted on ceramic substrate (900mm ² \times 0.8mm)	R _{θJA}	156.2	°C/W	

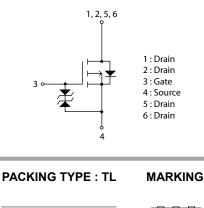


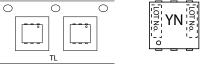
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VDSS	R _{DS} (on) Max	ID Max
	150mΩ@ –10V	
-30V	255mΩ@ –4.5V	-2A
	292mΩ@ –4V	

ELECTRICAL CONNECTION P-Channel





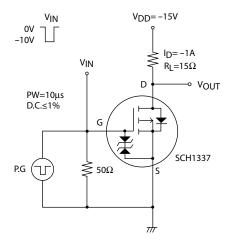
ORDERING INFORMATION See detailed ordering and shipping information on page 5 of this data sheet.

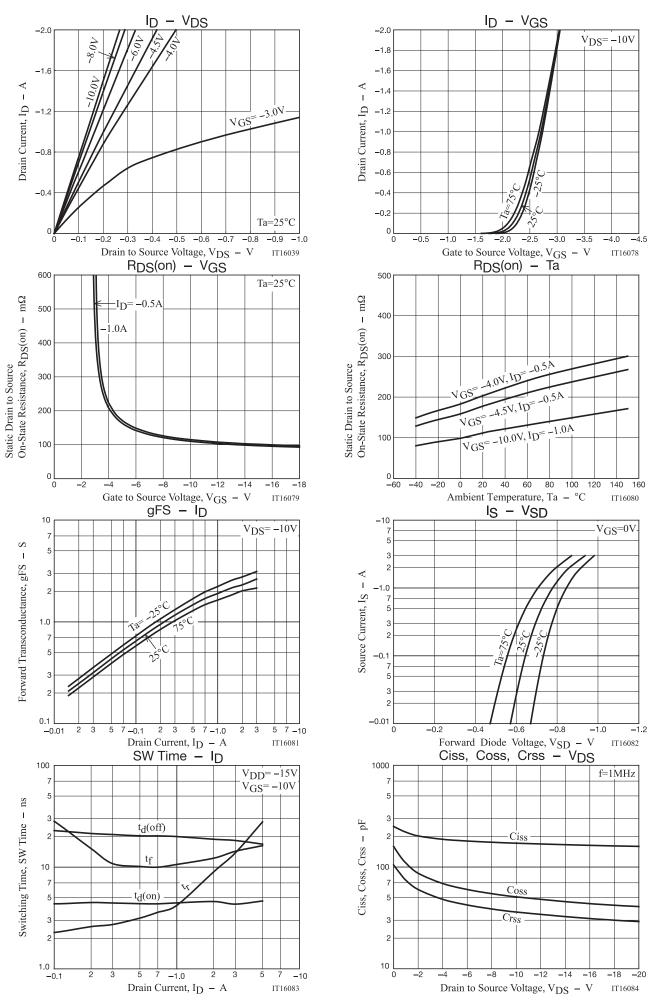
Parameter	Symbol	Conditions	Value			Unit
Falameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-30			V
Zero-Gate Voltage Drain Current	IDSS VDS=-30V, VGS=0V				-1	μA
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	VGS(th)	V _{DS} =-10V, I _D =-1mA	-1.2		-2.6	V
Forward Transconductance	9FS	V _{DS} =-10V, I _D =-1A		1.9		S
	R _{DS} (on)1	ID=-1A, VGS=-10V		115	150	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	ID=-0.5A, VGS=-4.5V		182	255	mΩ
Resistance	R _{DS} (on)3	ID=-0.5A, VGS=-4V		208	292	mΩ
Input Capacitance	Ciss			172		pF
Output Capacitance	Coss	V _{DS} =–10V, f=1MHz		51		pF
Reverse Transfer Capacitance	Crss			36		pF
Turn-ON Delay Time	t _d (on)			4.5		ns
Rise Time	tr			4.2		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		20		ns
Fall Time	tf			10.6		ns
Total Gate Charge	Qg			3.9		nC
Gate to Source Charge	Qgs	V _{DS} =-15V, V _{GS} =-10V, I _D =-2A		0.6		nC
Gate to Drain "Miller" Charge	Qgd			0.8		nC
Forward Diode Voltage	V _{SD}	IS=-2A, VGS=0V		-0.86	-1.5	V

ELECTRICAL CHARACTERISTICS at $Ta = 25^{\circ}C$ (Note 3)

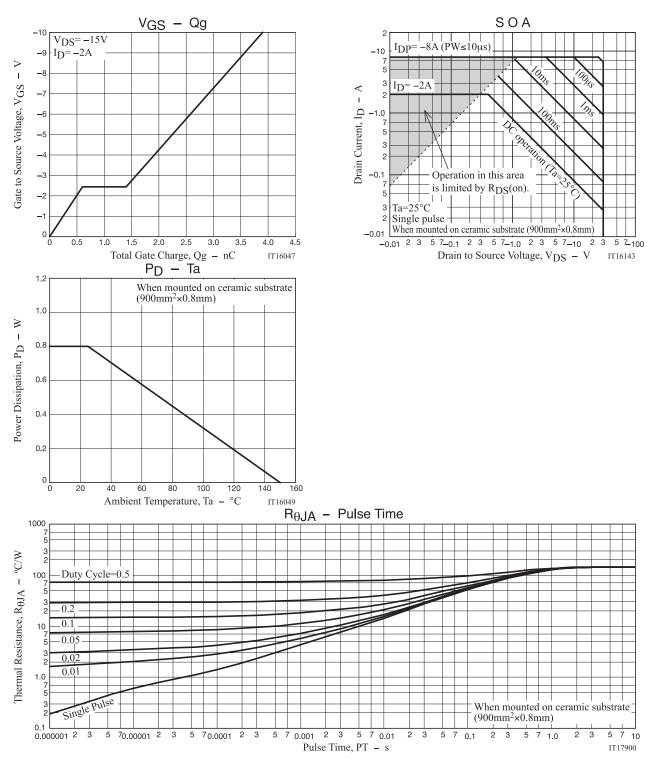
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





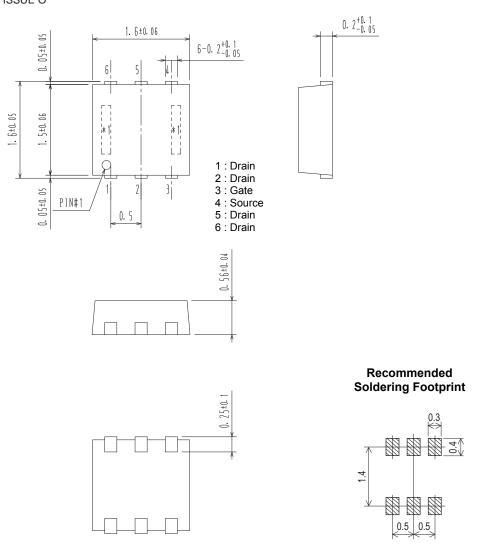
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PACKAGE DIMENSIONS

unit : mm

SOT-563 / SCH6 CASE 463AB ISSUE O



ORDERING INFORMATION

	Device	Marking	Package	Shipping (Qty / Packing)		
	SCH1337-TL-H	YN	SOT-563 / SCH6	5,000 / Tape & Reel		
	SCH1337-TL-W	YN	(Pb-Free / Halogen Free)			

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the SCH1337 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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